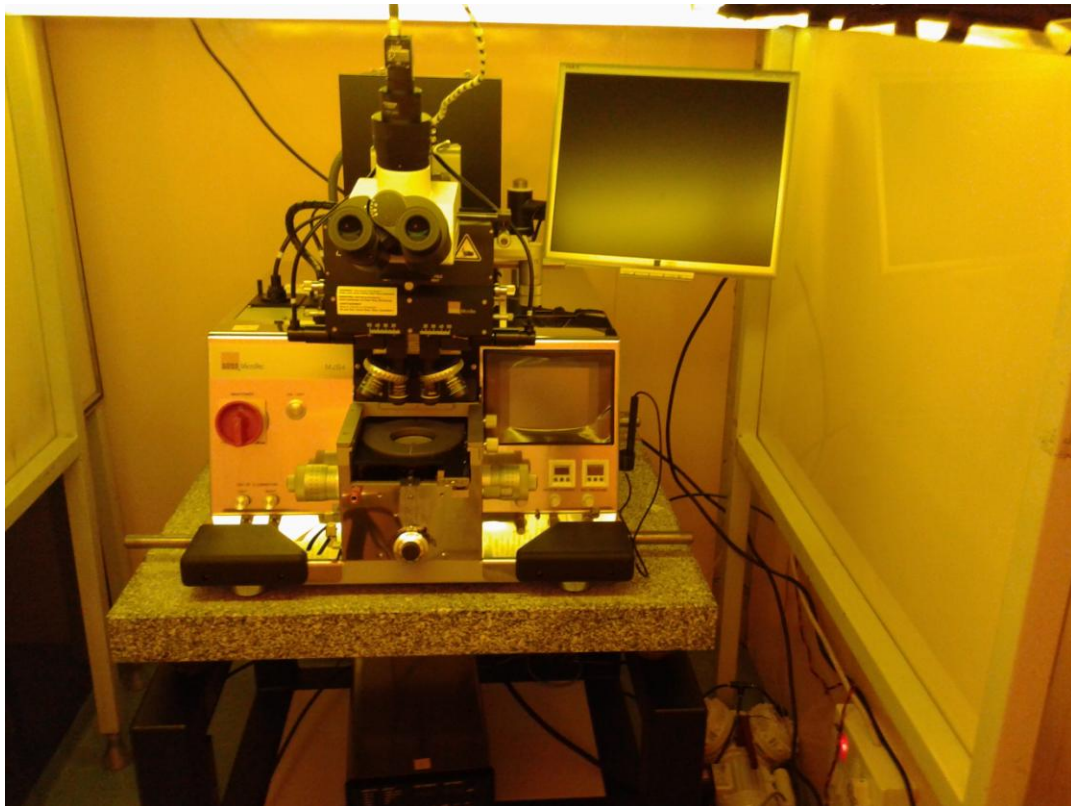


KARL SUSS MJB4 MASK ALIGNER

Optical lithography is a process use in micro fabrication to selectively create patterns in light sensitive materials (photo resist). It uses light to transfer geometric pattern from a photo mask to a light sensitive photo resist on a substrate. A mask aligner is use to expose a photo resist coated substrate to UV light through a photo mask which casts a shadow on a surface to define the photo resist mask.



Specifications of MJB-4 Standard Mask Aligner:

Configured for Top side alignment (TSA).

- **Primary exposure wavelength :-** 365nm-405nm (350 watt mercury lamp)
- **Support Substrates :-** 2”- 4” diameter
- **UV Lamp :-** 350 W Hg arc lamp & 500 W Hg arc lamp
- **Support Mask :-** 3”-5”
- **Line/Space resolution :-** 0.6 μ m
- **Alignment Accuracy :-** 0.2 μ m
- **Lithography Type:** - Soft contact mode, Vacuum mode, Low-vacuum mode, Gap mode, hard contact mode.
- **Substrate Size:** - Max. size - 4” and min. size – quarter or less 2” wafers.